freescale

飞思卡尔(深圳)功率半导体有限公司

TK8P25DA
MOSFETs   Silicon N-Channel MOS (π-MOSⅦ)
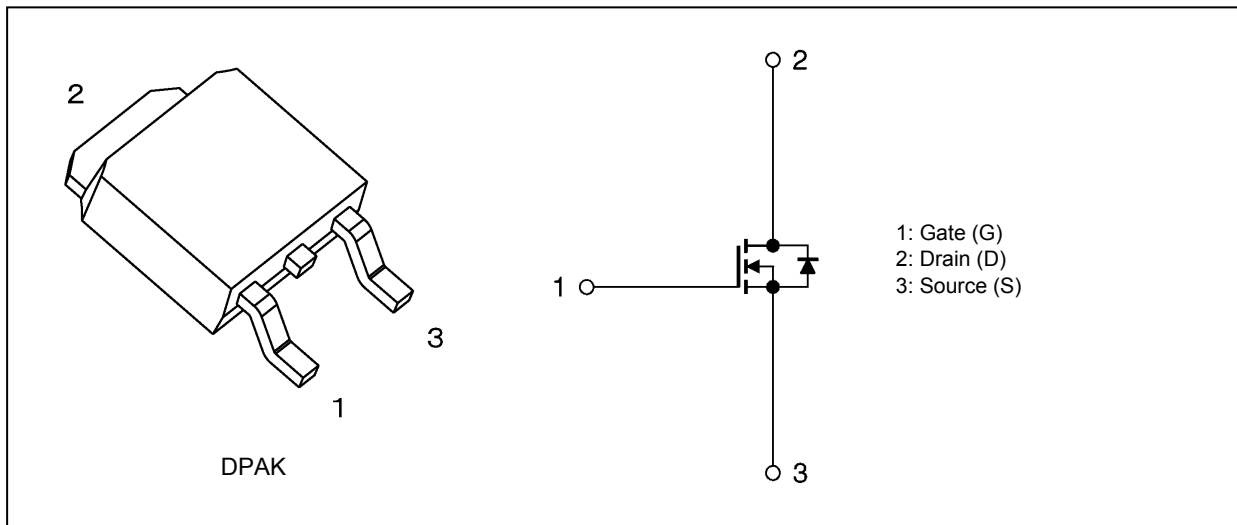
1. Applications

· Switching Voltage Regulators

2. Features

(1) Low drain-source on-resistance: $R_{DS(ON)}$ = 0.41 Ω (typ.)

(2) Low leakage current: I_{DSS} = 10 μA (max) (V_{DS} = 250 V)

(3) Enhancement mode: V_{th} = 1.5 to 3.5 V (V_{DS} = 10 V, I_D = 1 mA)

3. Packaging and Internal Circuit

DPAK

1: Gate (G)
2: Drain (D)
3: Source (S)

4. Absolute Maximum Ratings (Note) (T_a = 25℃ unless otherwise specified)

Characteristics		Symbol	Rating	Unit
Drain-source voltage		V_{DSS}	250	V
Gate-source voltage		V_{GSS}	±20	
Drain current (DC)	(Note 1)	I_D	7.5	A
Drain current (pulsed)	(Note 1)	I_{DP}	30	
Power dissipation	(T_c = 25℃)	P_D	55	W
Single-pulse avalanche energy	(Note 2)	E_{AS}	45	mJ
Avalanche current	(Note 3)	I_{AR}	7.5	A
Reverse drain current (DC)	(Note 1)	I_{DR}	7.5	
Reverse drain current (pulsed)	(Note 1)	I_{DRP}	30	
Channel temperature		T_{ch}	150	℃
Storage temperature		T_{stg}	-55 to 150	

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

5. Thermal Characteristics

Characteristics	Symbol	Max	Unit
Channel-to-case thermal resistance	$R_{th(ch-c)}$	2.27	°C/W
Channel-to-ambient thermal resistance	$R_{th(ch-a)}$	125	

Note 1: Ensure that the channel temperature does not exceed 150°C.

Note 2: V_{DD} = 50 V, T_{ch} = 25°C (initial), L = 1.33 mH, R_G = 25 Ω, I_{AR} = 7.5 A

Note 3: Repetitive rating; pulse width limited by maximum channel temperature

Note: This transistor is sensitive to electrostatic discharge and should be handled with care.

6. Electrical Characteristics

6.1. Static Characteristics (T_a = 25℃ unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Gate leakage current	I_{GSS}	V_{GS} = ±20 V, V_{DS} = 0 V	—	—	±1	μA
Drain cut-off current	I_{DSS}	V_{DS} = 250 V, V_{GS} = 0 V	—	—	10	
Drain-source breakdown voltage	$V_{(BR)DSS}$	I_D = 10 mA, V_{GS} = 0 V	250	—	—	V
Gate threshold voltage	V_{th}	V_{DS} = 10 V, I_D = 1 mA	1.5	—	3.5	
Drain-source on-resistance	$R_{DS(ON)}$	V_{GS} = 10 V, I_D = 3.8 A	—	0.41	0.5	Ω

6.2. Dynamic Characteristics (T_a = 25℃ unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Input capacitance	C_{iss}	V_{DS} = 100 V, V_{GS} = 0 V, f = 1 MHz	—	550	—	pF
Reverse transfer capacitance	C_{rss}		—	5.1	—	
Output capacitance	C_{oss}		—	40	—	
Gate resistance	r_g	V_{DS} = OPEN, f = 1 MHz	—	5.8	—	Ω
Switching time (rise time)	t_r	See Figure 6.2.1.	—	28	—	ns
Switching time (turn-on time)	t_{on}		—	32	—	
Switching time (fall time)	t_f		—	16	—	
Switching time (turn-off time)	t_{off}		—	66	—	
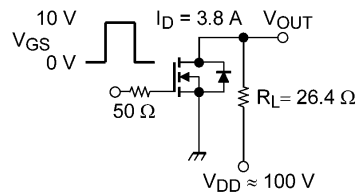
Duty ≤ 1%, t_w = 10 μs

Fig. 6.2.1   Switching Time Test Circuit

6.3. Gate Charge Characteristics (T_a = 25℃ unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Total gate charge (gate-source plus gate-drain)	Q_g	V_{DD} ≈ 200 V, V_{GS} = 10 V, I_D = 7.5 A	—	16	—	nC
Gate-source charge 1	Q_{gs1}		—	3.3	—	
Gate-drain charge	Q_{gd}		—	5.3	—	

6.4. Source-Drain Characteristics (T_a = 25℃ unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Diode forward voltage	V_{DSF}	I_{DR} = 7.5 A, V_{GS} = 0 V	—	—	-1.7	V
Reverse recovery time	t_{rr}	I_{DR} = 7.5 A, V_{GS} = 0 V -dI_{DR}/dt = 100 A/μs	—	150	—	ns
Reverse recovery charge	Q_{rr}		—	0.8	—	μC
Peak reverse recovery current	I_{rr}		—	11	—	A

7. Marking

TK8P25DA ← ——— Part No. (or abbreviation code)
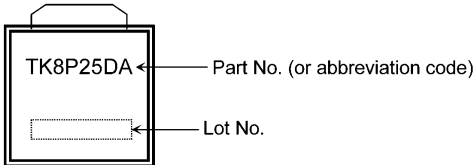
← ——— Lot No.

Fig. 7.1   Marking

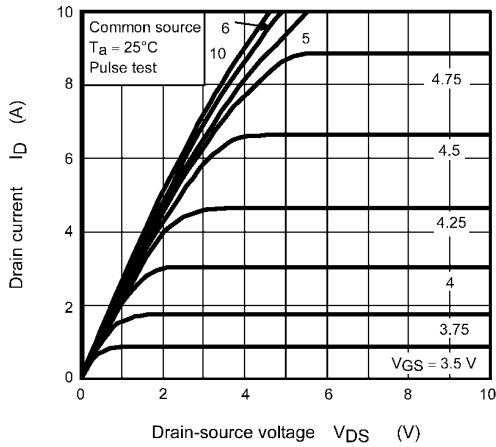# 8. Characteristics Curves (Note)
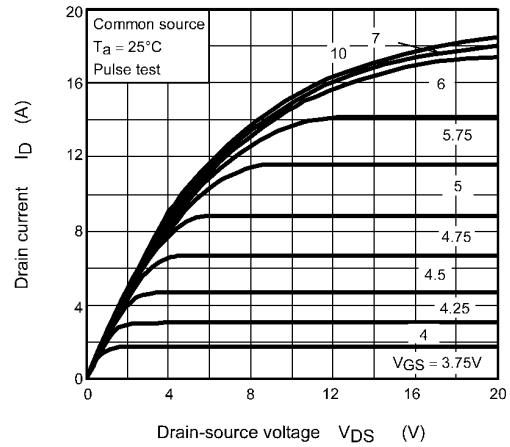

Fig. 8.1 I_D - V_{DS}
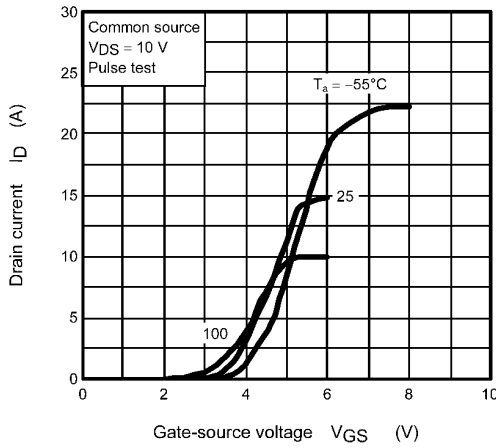

Fig. 8.2 I_D - V_{DS}
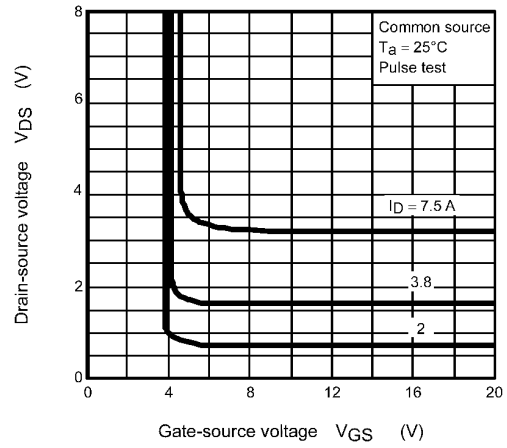

Fig. 8.3 I_D - V_{GS}
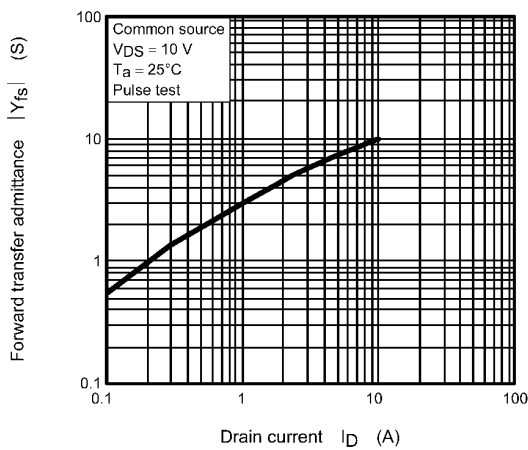

Fig. 8.4 V_{DS} - V_{GS}
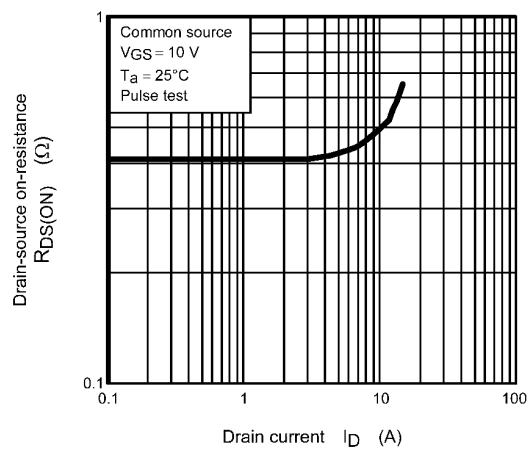

Fig. 8.5 $|Y_{fs}|$ - I_D
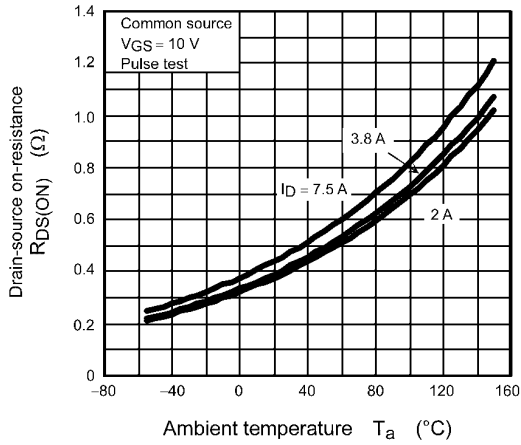

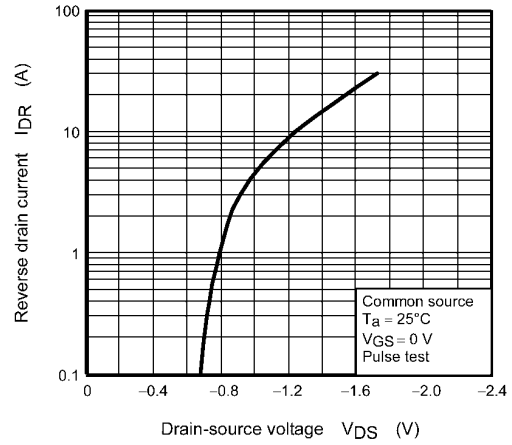Fig. 8.6 $R_{DS(ON)}$ - I_D

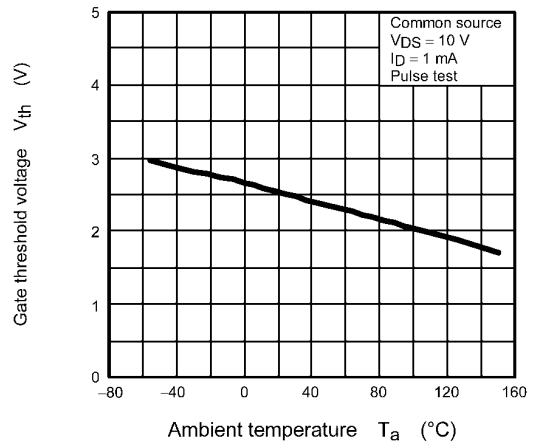Fig. 8.7 $R_{DS(ON)} - T_a$

Fig. 8.8 $I_{DR} - V_{DS}$
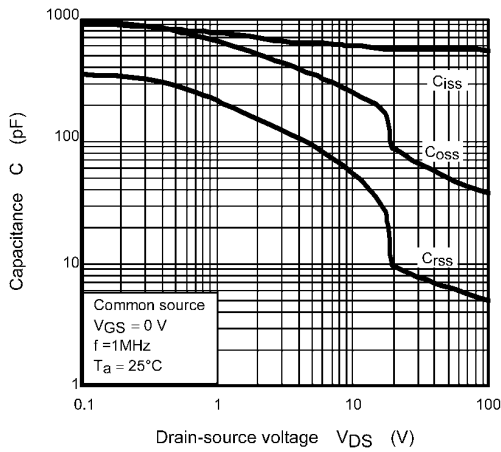
Fig. 8.9 $C - V_{DS}$
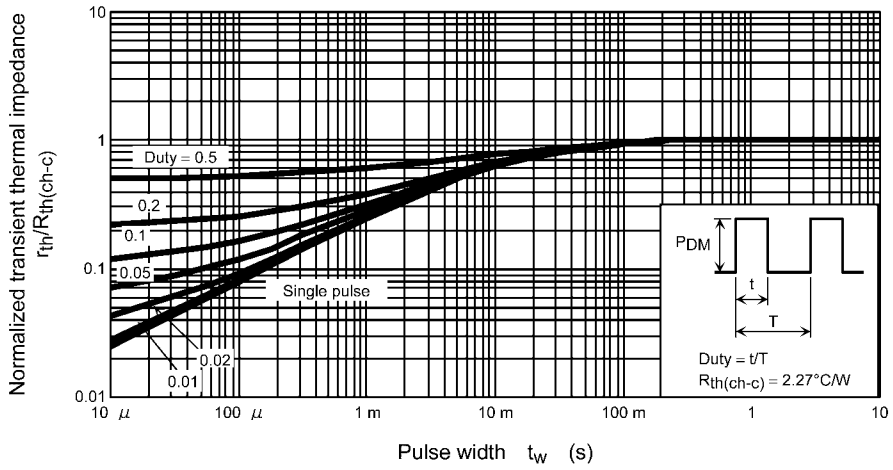
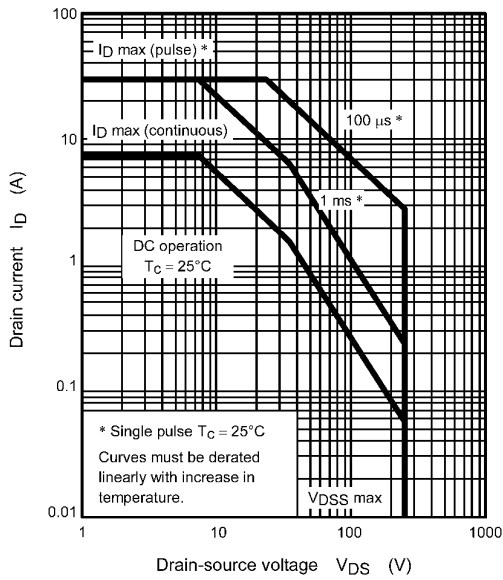Fig. 8.10 $V_{th} - T_a$
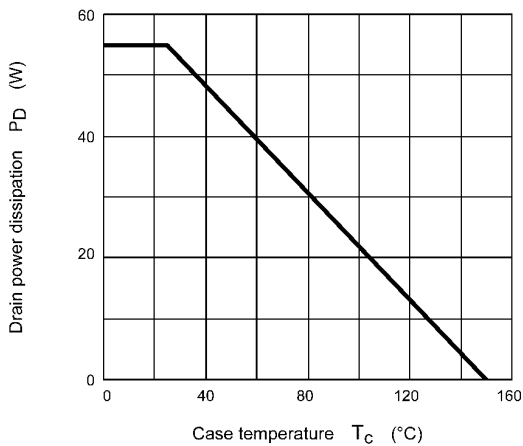
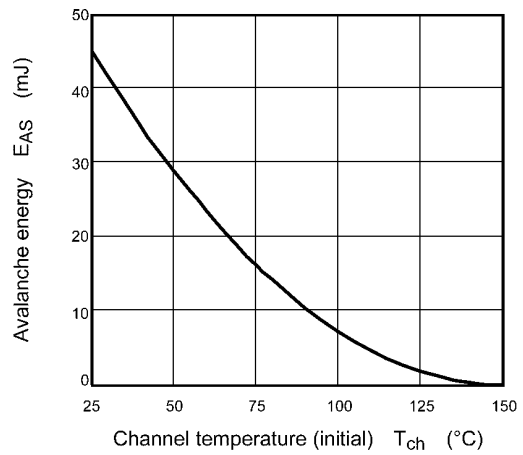Fig. 8.11 $P_D - T_c$
(Guaranteed Maximum)
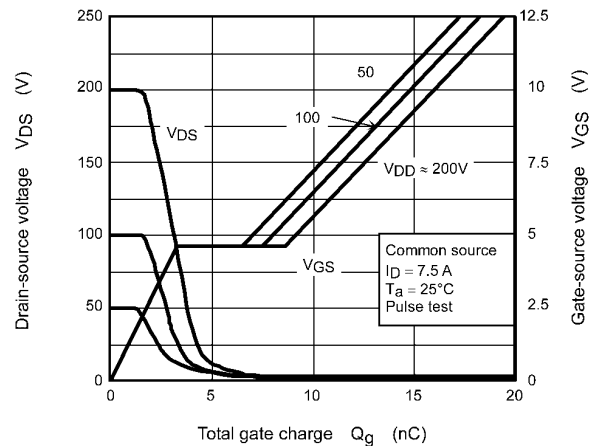
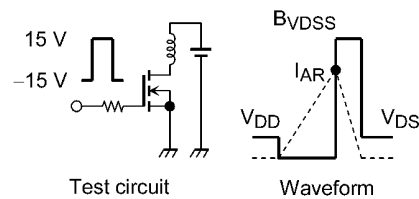Fig. 8.12 Dynamic Input/Output Characteristics

Fig. 8.13 $r_{th}/R_{th(ch-c)} - t_w$
(Guaranteed Maximum)

Fig. 8.14 Safe Operating Area
(Guaranteed Maximum)

Fig. 8.15 $E_{AS} - T_{ch}$
(Guaranteed Maximum)

Test circuit   Waveform

$R_G = 25\ \Omega$
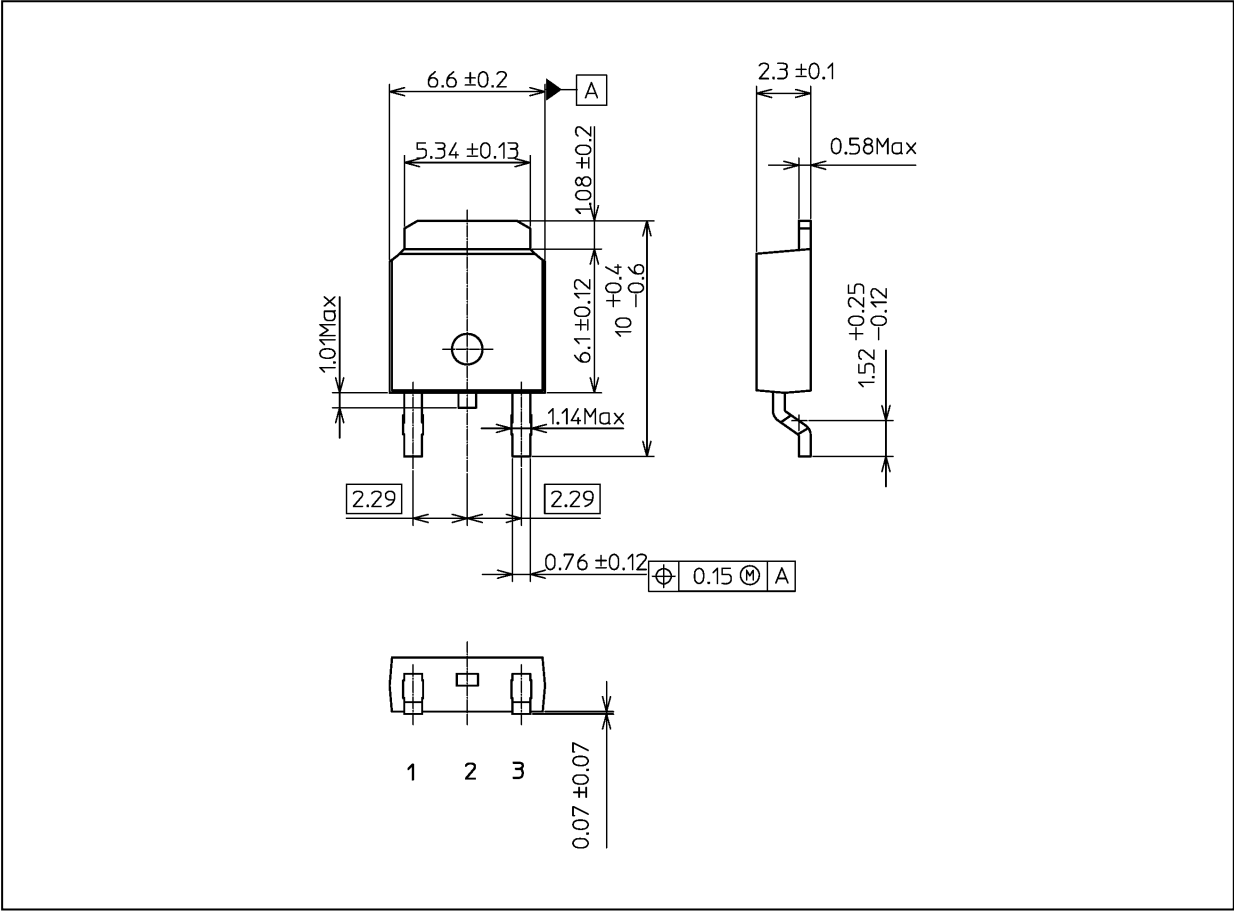$V_{DD} = 50\ V,\ L = 1.33\ mH$

$$E_{AS} = \frac{1}{2} \cdot L \cdot I^2 \cdot \left(\frac{B_{VDSS}}{B_{VDSS} - V_{DD}} \right)$$

Fig. 8.16 Test Circuit/Waveform

Package Dimensions

Unit: mm

Weight: 0.36 g (typ.)